



PD55025-E PD55025S-E

RF POWER transistor, LDMOST plastic family N-Channel enhancement-mode lateral MOSFETs

General features

- Excellent thermal stability
- Common source configuration
- $P_{OUT} = 25W$ with 14.5dB gain @ 500MHz / 12.5V
- New RF plastic package

Description

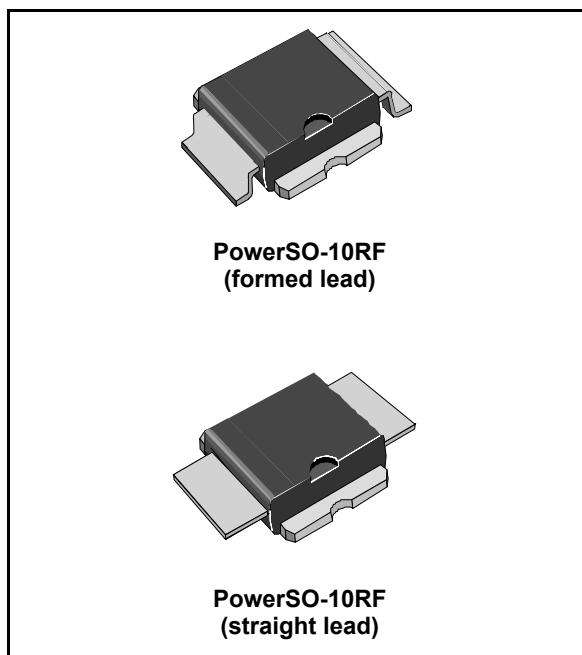
The PD55025 is a common source N-Channel, enhancement-mode lateral Field-Effect RF power transistor. It is designed for high gain, broad band commercial and industrial applications. It operates at 12 V in common source mode at frequencies of up to 1 GHz. PD55025 boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in the first true SMD plastic RF power package, PowerSO-10RF. PD55025's superior linearity performance makes it an ideal solution for car mobile radio.

The PowerSO-10 plastic package, designed to offer high reliability, is the first ST JEDEC approved, high power SMD package. It has been specially optimized for RF needs and offers excellent RF performances and ease of assembly.

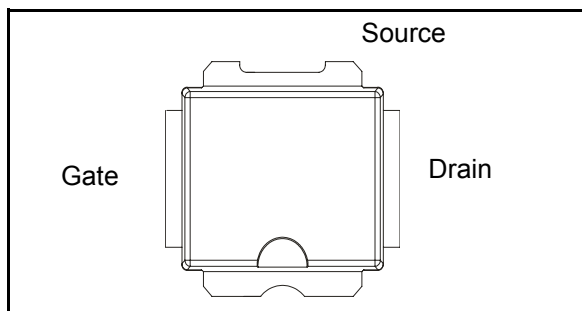
Mounting recommendations are available in www.st.com/rf/ (look for application note AN1294)

Order codes

Part number	Package	Packing
PD55025-E	PowerSO-10RF (formed lead)	Tube
PD55025S-E	PowerSO-10RF (straight lead)	Tube
PD55015TR-E	PowerSO-10RF (formed lead)	Tape and reel
PD55015STR-E	PowerSO-10RF (straight lead)	Tape and reel



Pin connection



Contents

1	Electrical data	3
1.1	Maximum ratings	3
1.2	Thermal data	3
2	Electrical Characteristics	4
2.1	Static	4
2.2	Dynamic	4
3	Impedance	5
4	Typical performance	6
5	Test circuit	11
6	Circuit layout	12
7	Common source s-parameter	14
7.1	PD55025S (VDS = 12.5V ID = 500mA)	14
7.2	PD55025S (VDS = 12.5V ID = 1.5A)	14
7.3	PD55025S (VDS = 12.5V ID = 3A)	15
7.4	PD55025S (VDS = 13.8V IDS = 3A)	15
8	Package mechanical data	16
9	Revision history	21

1 Electrical data

1.1 Maximum ratings

Table 1. Absolute maximum ratings ($T_{CASE} = 25^{\circ}C$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-source voltage	40	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current	7	A
P_{DISS}	Power dissipation (@ $T_C = 70^{\circ}C$)	79	W
T_J	Max. operating junction temperature	165	$^{\circ}C$
T_{STG}	Storage temperature	-65 to +150	$^{\circ}C$

1.2 Thermal data

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Junction - case thermal resistance	1.2	$^{\circ}C/W$

2 Electrical Characteristics

$$T_{CASE} = +25\text{ }^{\circ}\text{C}$$

2.1 Static

Table 3. Static

Symbol	Test conditions			Min.	Typ.	Max.	Unit
I_{DSS}	$V_{GS} = 0V$	$V_{DS} = 28V$				1	μA
I_{GSS}	$V_{GS} = 20V$	$V_{DS} = 0V$				1	μA
$V_{GS(Q)}$	$V_{DS} = 28V$	$I_D = 100mA$		2.0		5.0	V
$V_{DS(ON)}$	$V_{GS} = 10V$	$I_D = 3A$			0.7	0.8	V
G_{FS}	$V_{DS} = 10V$	$I_D = 3A$		2.5			mho
C_{ISS}	$V_{GS} = 0V$	$V_{DS} = 12.5V$	$f = 1MHz$		86		pF
C_{OSS}	$V_{GS} = 0V$	$V_{DS} = 12.5V$	$f = 1MHz$		76		pF
C_{RSS}	$V_{GS} = 0V$	$V_{DS} = 12.5V$	$f = 1MHz$		5.8		pF

2.2 Dynamic

Table 4. Dynamic

Symbol	Test conditions			Min.	Typ.	Max.	Unit
P_{OUT}	$V_{DD} = 12.5V, I_{DQ} = 200mA$	$f = 500MHz$		25			W
G_P	$V_{DD} = 12.5V, I_{DQ} = 200mA, P_{OUT} = 25W, f = 500MHz$				14.5		dB
h_D	$V_{DD} = 12.5V, I_{DQ} = 200mA, P_{OUT} = 25W, f = 500MHz$				50		%
Load mismatch	$V_{DD} = 15.5V, I_{DQ} = 200mA, P_{OUT} = 25W, f = 500MHz$ All phase angles			20:1			VSWR

3 Impedance

Figure 1. Current conventions

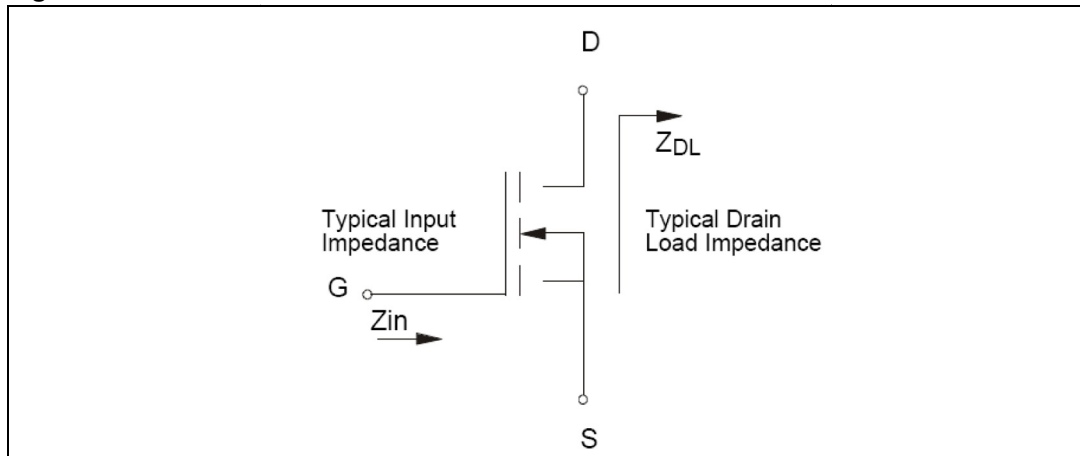


Table 5. Impedance data

Freq. (MHz)	$Z_{IN} (\Omega)$	$Z_{DL} (\Omega)$
175	$3.20 - j 4.41$	$1.56 + j 2.14$
480	$1.01 - j 1.67$	$1.06 + j 0.22$
500	$0.93 - j 1.53$	$1.12 + j 0.20$
520	$0.88 - j 1.98$	$1.07 + j 0.83$

4 Typical performance

Figure 2. Capacitance vs supply voltage

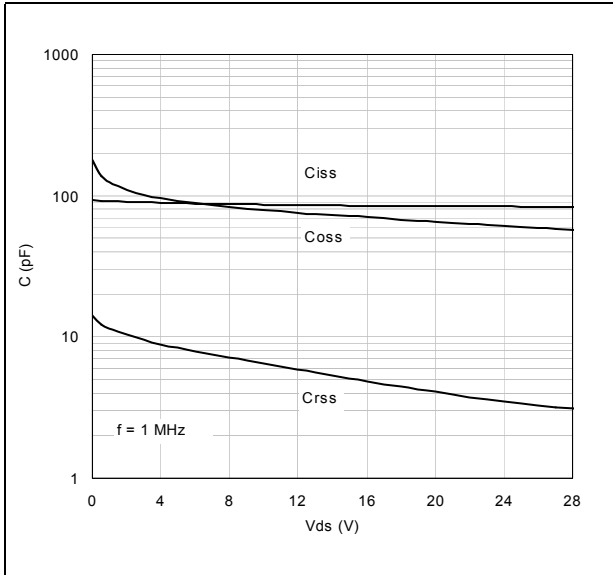


Figure 3. Drain current vs gate source voltage

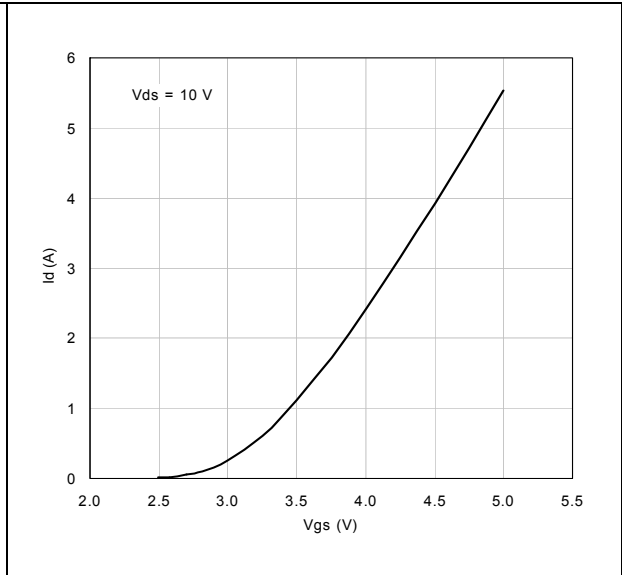


Figure 4. Gate-source voltage vs case temperature

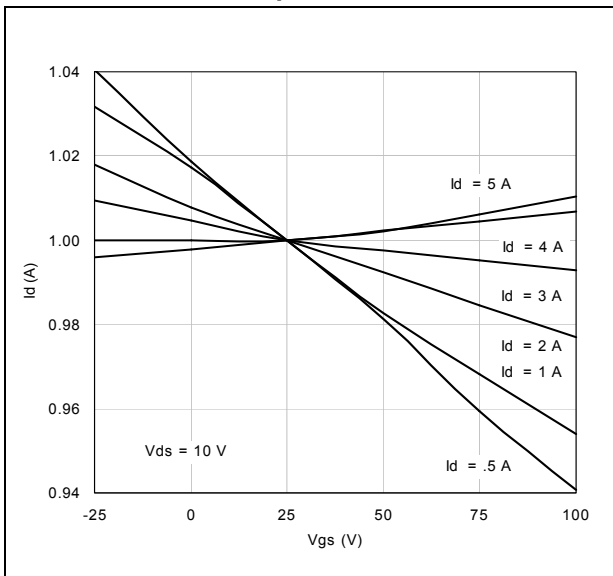


Figure 5. Output power vs input power

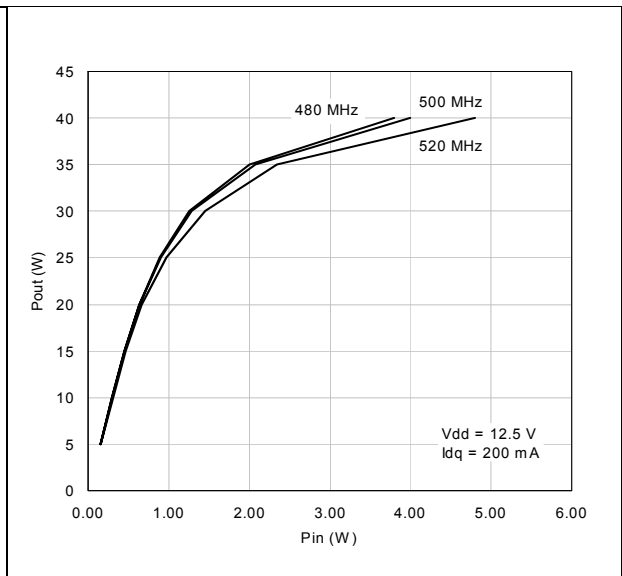


Figure 6. Output power vs input power

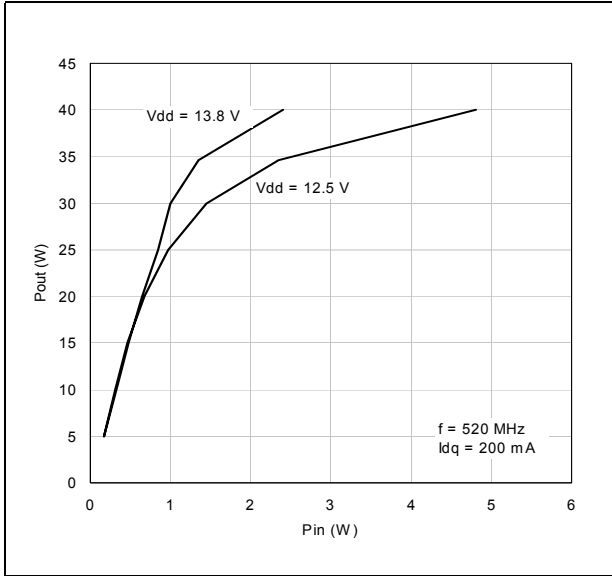


Figure 7. Power gain vs. output power

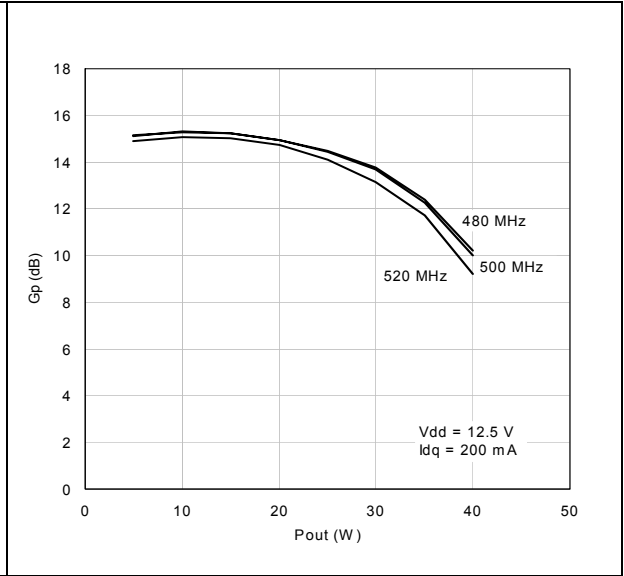


Figure 8. Drain efficiency vs output power

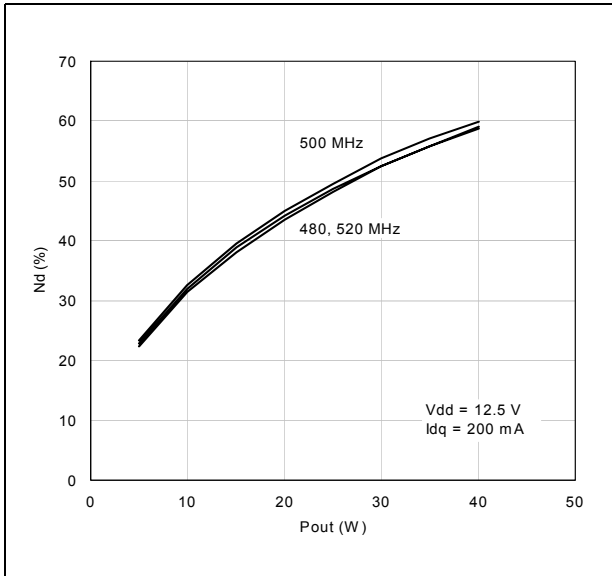


Figure 9. Input return loss vs output power

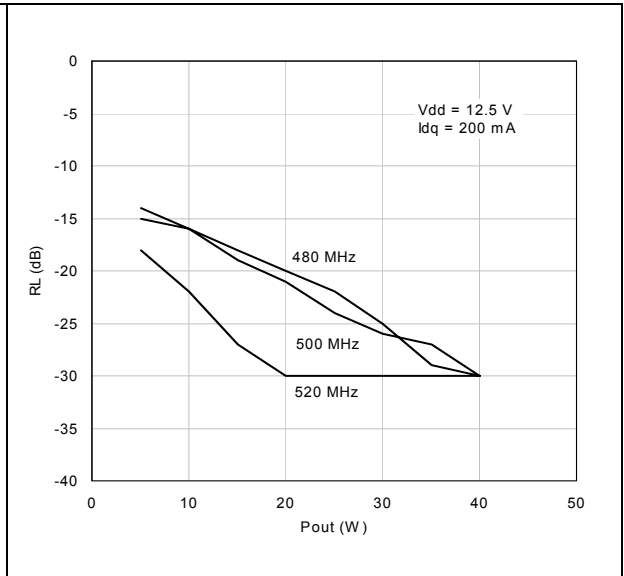


Figure 10. Output power vs bias current

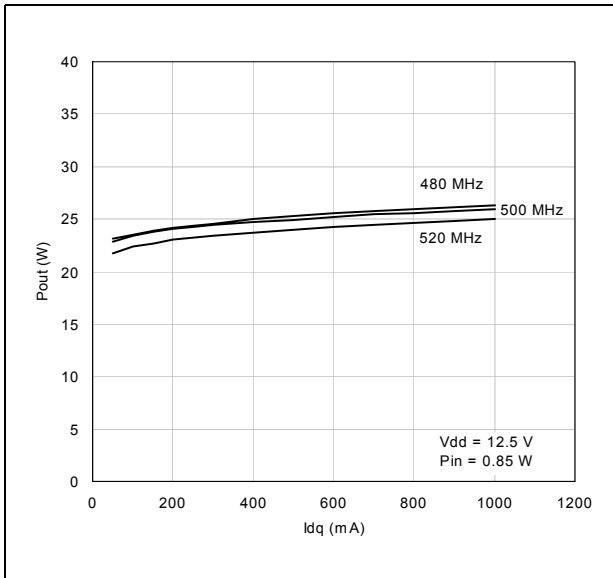


Figure 11. Drain efficiency vs bias current

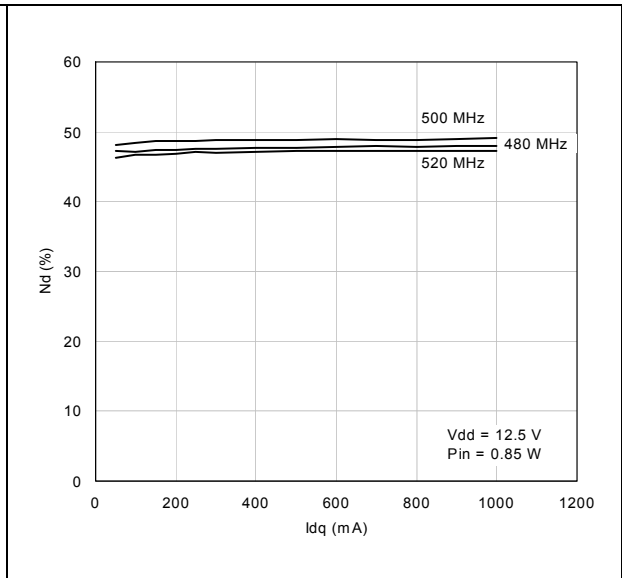


Figure 12. Output power vs supply voltage

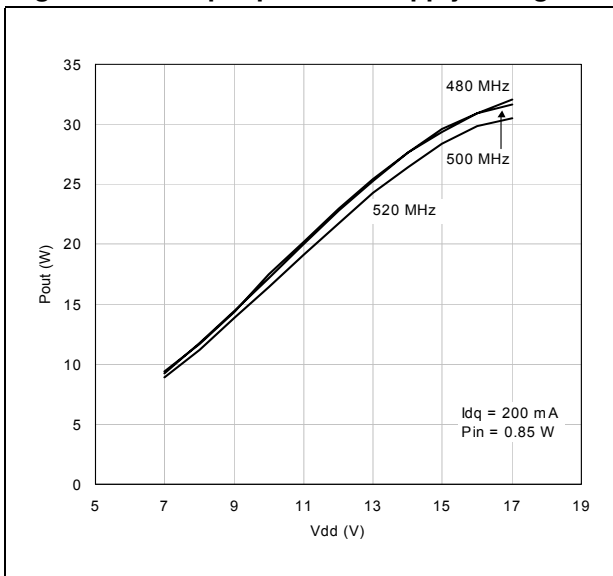


Figure 13. Drain efficiency vs supply voltage

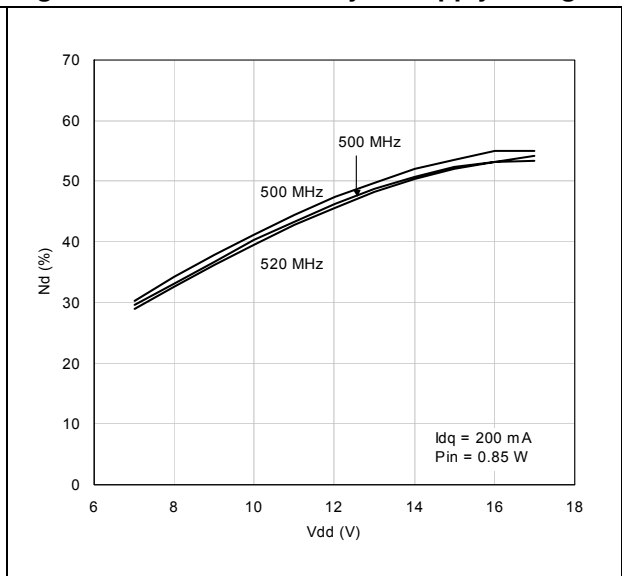


Figure 14. Output power vs gate bias voltage

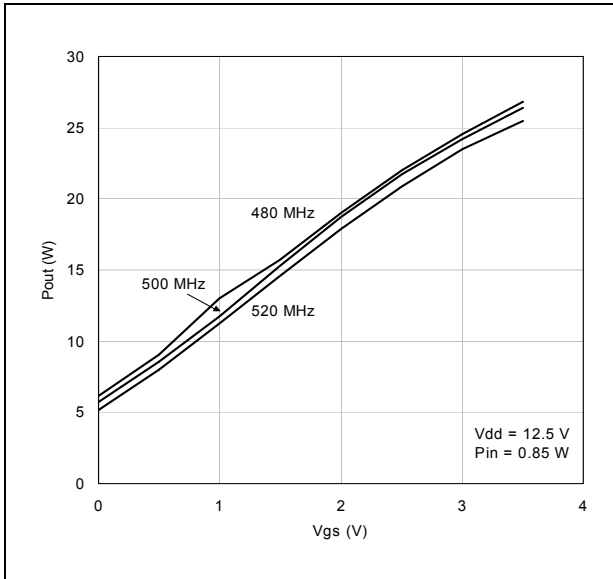


Figure 15. Output power vs input power (f = 175 MHz)

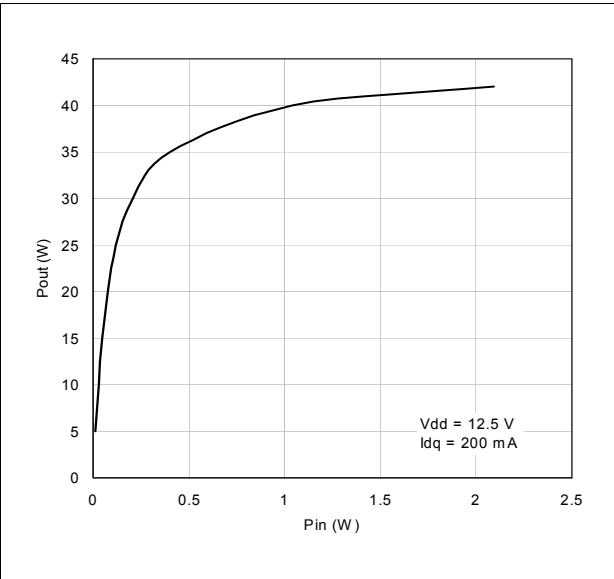


Figure 16. Power gain vs output power (f = 175 MHz)

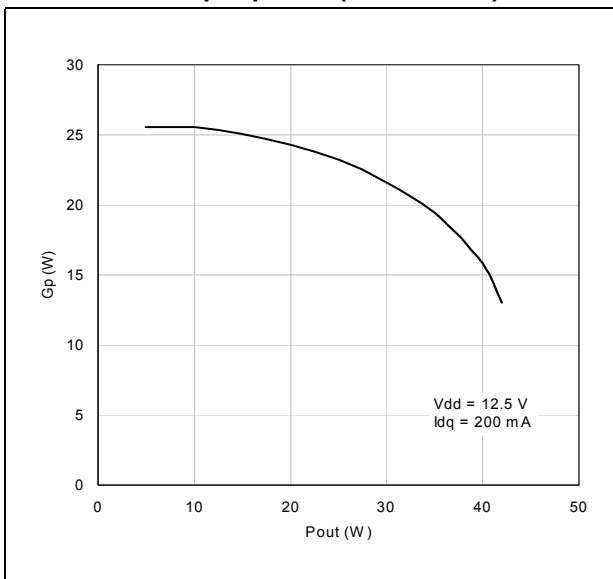


Figure 17. Drain efficiency vs output power (f = 175 MHz)

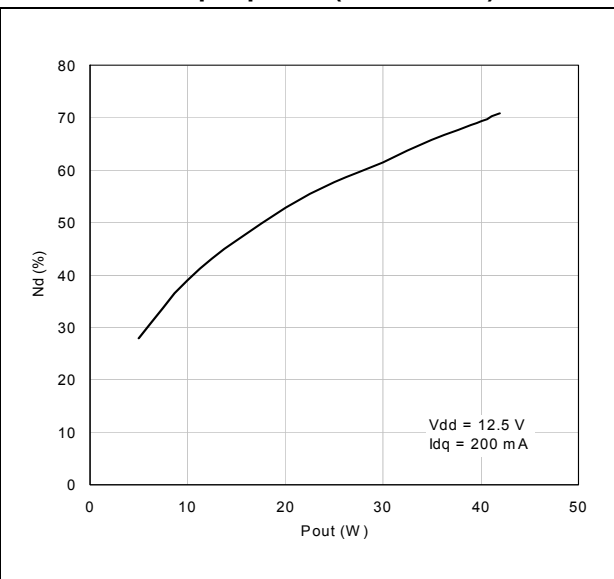
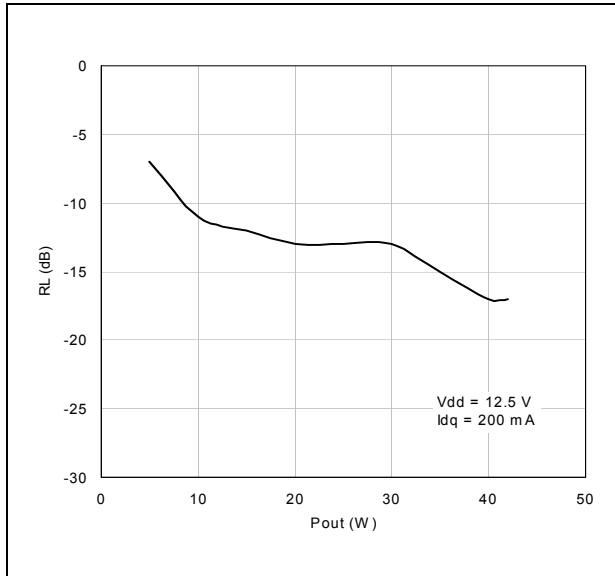


Figure 18. Input return loss vs output power (f = 175 MHz)



5 Test circuit

Figure 19. 500MHz test circuit schematic (engineering)

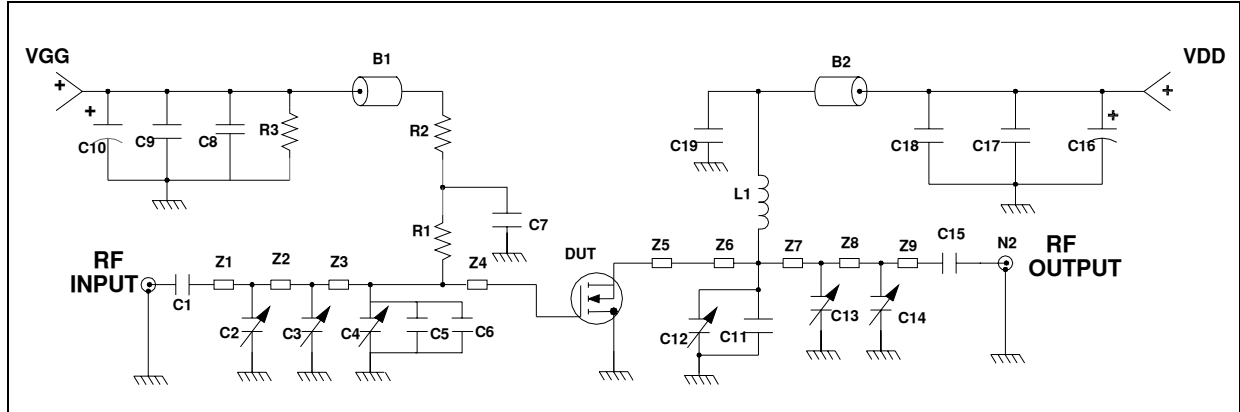


Table 6. Test circuit component part list

Component	Description
B1,B2	FERRITE BEAD
C1,C13	300 pF, 100 mil CHIP CAPACITOR
C2,C3,C4,C12,C13,C14	1 to 20 pF TRIMMER CAPACITOR
C6	39 pF ATC 100B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C7, C19	120 pF 100 mil CHIP CAPACITOR
C10, C16	10 μ F, 50 V ELECTROLYTIC CAPACITOR
C9, C17	0.1 mF, 100 mil CHIP CAP
C8, C18	1.000 pF 100 mil CHIP CAP
C5, C11	33 pF, 100 mil CHIP CAP
L1	56 nH, 7 TURN, COILCRAFT
N1, N2	TYPE N FLANGE MOUNT
R1	15 Ω , 1 W CHIP RESISTOR
R2	1 K Ω , 1 W CHIP RESISTOR
R3	33 K Ω , 1 W CHIP RESISTOR
Z1	0.471" X 0.080" MICROSTRIP
Z2	1.082" X 0.080" MICROSTRIP
Z3	0.372" X 0.080" MICROSTRIP
Z4,Z5	0.260" X 0.223" MICROSTRIP
Z6	0.050" X 0.080" MICROSTRIP
Z7	0.551" X 0.080" MICROSTRIP
Z8	0.825" X 0.080" MICROSTRIP
Z9	0.489" X 0.080" MICROSTRIP
BOARD	ROGER, ULTRA LAM 2000 THK 0.030", $\epsilon_r = 2.55$ 2oz. ED cu 2 SIDES.

6 Circuit layout

Figure 20. 500MHz test circuit

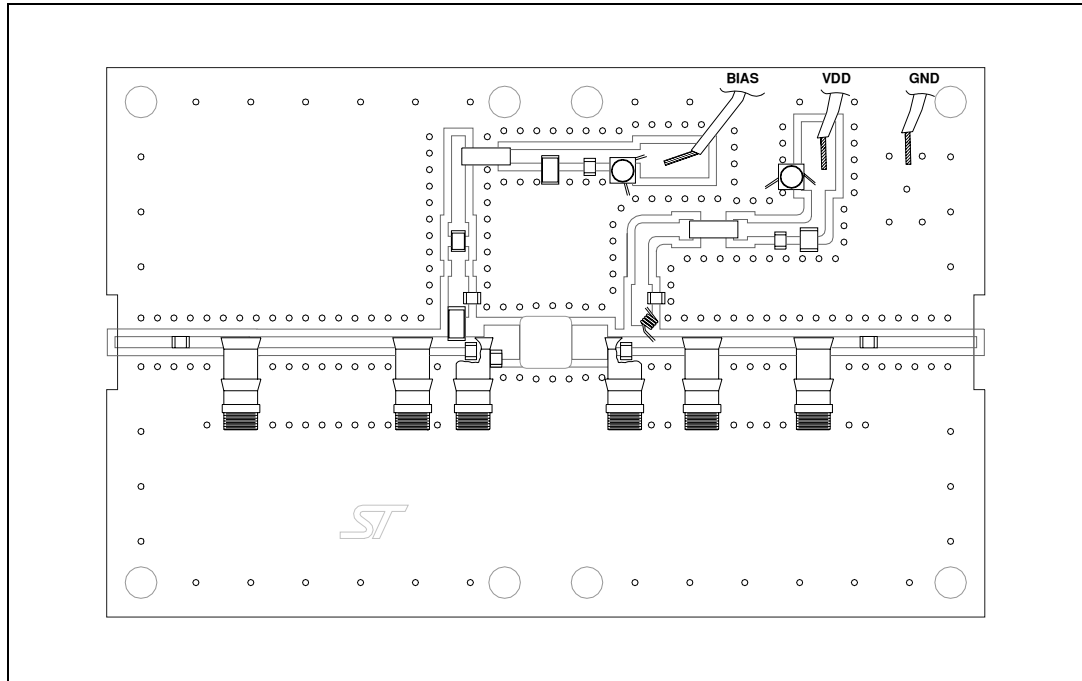


Figure 21. 500MHz test circuit photomaster

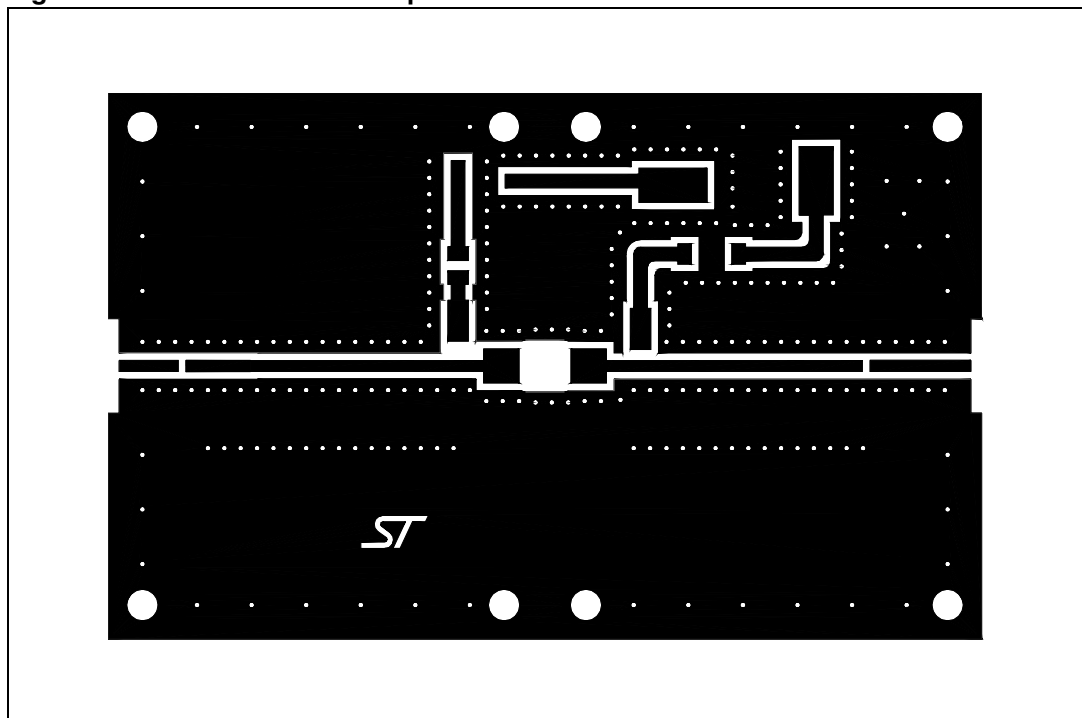


Figure 22. 175MHz test circuit schematic (engineering)

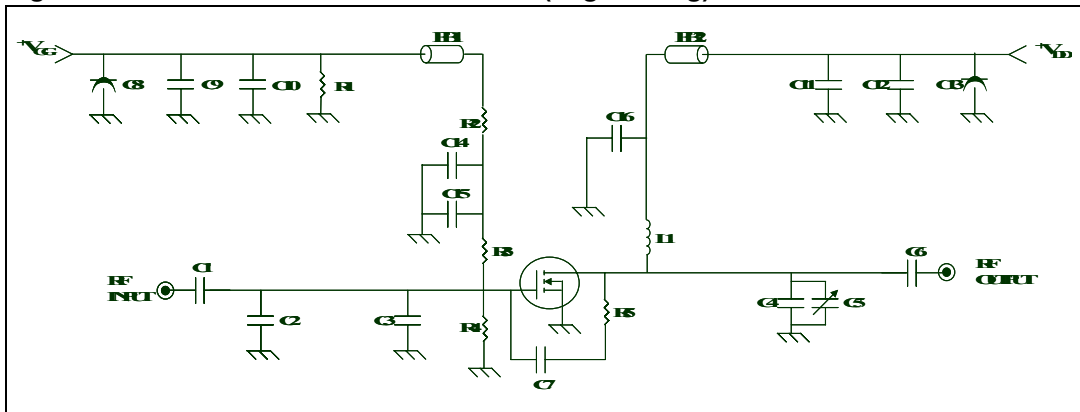


Table 7. 175MHz test circuit component part list

Component	Description
C1, C6	300 pF CHIP CAPACITOR
C2, C3	91 pF CHIP CAPACITOR
C4, C14	75 pF CHIP CAPACITOR
C5	1-20 pF TRIMMER CAPACITOR
C7	.01 μ F MOLDED CAPACITOR
C8, C13	10 μ F ELECTROLYTIC CAPACITOR
C9, C12	.1 μ F CHIP CAPACITOR
C10, C11	1000 pF CHIP CAPACITOR
C15, C16	1200 pF CHIP CAPACITOR
FB1, FB2	FERRITE BEAD
R1	33 K Ω CHIP RESISTOR
R2	17 Ω CHIP RESISTOR
R3	15 Ω CHIP RESISTOR
R4	47 Ω CHIP RESISTOR
R5	220 Ω CHIP RESISTOR
L1	5 TURN, 16 AWG MAGNET WIRE, ID = .40", INDUCTOR
BOARD	ROGER, ULTRA LAM 2000, THK 0.030", $\epsilon_r = 2.55$ 2oz. ED cu 2 SIDES.

7 Common source s-parameter

7.1 PD55025S ($V_{DS} = 12.5V$ $I_D = 500mA$)

Table 8. S-parameter

FREQ (MHz)	S ₁₁	S ₁₁ ∠Φ	S ₂₁	S ₂₁ ∠Φ	S ₁₂	S ₁₂ ∠Φ	S ₂₂	S ₂₂ ∠Φ
50	0.837	-162	13.33	89	0.018	-1	0.780	-168
100	0.846	-169	6.51	76	0.017	-12	0.803	-172
150	0.862	-171	4.15	66	0.016	-19	0.831	-172
200	0.878	-173	2.93	58	0.015	-26	0.859	-172
250	0.895	-174	2.20	51	0.013	-31	0.874	-172
300	0.910	-174	1.71	45	0.012	-36	0.886	-173
350	0.921	-175	1.36	40	0.010	-40	0.892	-173
400	0.932	-176	1.11	35	0.009	-42	0.897	-175
450	0.941	-177	0.92	31	0.008	-43	0.915	-176
500	0.946	-178	0.78	27	0.007	-44	0.932	-177
550	0.953	-178	0.66	24	0.006	-43	0.946	-178
600	0.957	-179	0.57	21	0.005	-42	0.964	-179
650	0.960	-180	0.50	18	0.004	-39	0.975	-178
700	0.964	180	0.44	16	0.004	-34	0.976	-179
750	0.966	179	0.39	14	0.003	-29	0.981	-179
800	0.968	178	0.95	12	0.002	-15	0.979	-179
850	0.970	178	0.31	10	0.002	-2	0.964	-179
900	0.971	177	0.28	8	0.002	16	0.960	180
950	0.972	177	0.26	6	0.002	34	0.953	179
1000	0.972	176	0.23	5	0.003	45	0.940	178

7.2 PD55025S ($V_{DS} = 12.5V$ $I_D = 1.5A$)

Table 9. S-parameter

FREQ (MHz)	S ₁₁	S ₁₁ ∠Φ	S ₂₁	S ₂₁ ∠Φ	S ₁₂	S ₁₂ ∠Φ	S ₂₂	S ₂₂ ∠Φ
50	0.876	-164	13.87	90	0.013	1	0.823	-172
100	0.880	-172	6.87	79	0.012	-7	0.838	-175
150	0.887	-174	4.46	71	0.012	-13	0.855	-176
200	0.895	-175	3.22	64	0.011	-18	0.873	-175
250	0.905	-176	2.47	58	0.010	-22	0.879	-175
300	0.915	-176	1.96	52	0.009	-25	0.885	-175
350	0.922	-177	1.60	47	0.009	-28	0.886	-175
400	0.931	-178	1.32	42	0.008	-30	0.889	-177
450	0.938	-178	1.11	38	0.007	-31	0.906	-178
500	0.942	-179	0.95	34	0.006	-31	0.923	-179
550	0.948	-179	0.82	31	0.005	-30	0.937	-179
600	0.952	-180	0.71	28	0.005	-27	0.956	-179
650	0.954	180	0.63	25	0.004	-22	0.967	-179
700	0.959	179	0.55	22	0.003	-16	0.969	-179
750	0.961	178	0.49	20	0.003	-6	0.973	-179
800	0.963	178	0.45	17	0.003	3	0.970	-179
850	0.966	177	0.40	15	0.003	17	0.956	-180
900	0.967	177	0.36	13	0.003	27	0.952	179
950	0.968	176	0.33	11	0.003	38	0.945	179
1000	0.968	176	0.30	9	0.003	45	0.933	177

7.3 PD55025S ($V_{DS} = 12.5V$ $I_D = 3A$)

Table 10. S-parameter

FREQ (MHz)	S ₁₁	S ₁₁ ∠Φ	S ₂₁	S ₂₁ ∠Φ	S ₁₂	S ₁₂ ∠Φ	S ₂₂	S ₂₂ ∠Φ
50	0.890	-165	13.19	91	0.012	2	0.837	-174
100	0.892	-172	6.55	81	0.011	-6	0.846	-176
150	0.898	-174	4.28	73	0.011	-12	0.865	-176
200	0.904	-175	3.11	66	0.010	-15	0.879	-176
250	0.913	-176	2.39	60	0.010	-20	0.883	-176
300	0.921	-177	1.91	54	0.009	-23	0.889	-176
350	0.926	-177	1.57	49	0.008	-25	0.887	-176
400	0.935	-178	1.31	44	0.007	-27	0.889	-177
450	0.941	-179	1.10	40	0.007	-28	0.905	-179
500	0.944	-179	0.94	36	0.006	-27	0.921	-179
550	0.949	-180	0.82	33	0.005	-25	0.936	-180
600	0.953	180	0.71	29	0.004	-21	0.954	180
650	0.955	179	0.63	26	0.004	-17	0.964	-180
700	0.959	179	0.56	24	0.003	-10	0.965	-180
750	0.961	178	0.50	21	0.003	-2	0.968	-180
800	0.963	177	0.45	19	0.003	10	0.966	-179
850	0.966	177	0.41	17	0.003	22	0.952	-180
900	0.967	176	0.37	15	0.003	32	0.948	180
950	0.968	176	0.34	15	0.003	41	0.942	179
1000	0.969	175	0.31	11	0.004	49	0.930	177

7.4 PD55025S ($V_{DS} = 13.8V$ $I_{DS} = 3A$)

Table 11. S-parameter

FREQ (MHz)	S ₁₁	S ₁₁ ∠Φ	S ₂₁	S ₂₁ ∠Φ	S ₁₂	S ₁₂ ∠Φ	S ₂₂	S ₂₂ ∠Φ
50	0.849	-164	13.99	91	0.012	2	0.833	-173
100	0.881	-171	6.94	80	0.011	-6	0.841	-175
150	0.895	-173	4.51	72	0.011	-12	0.857	-175
200	0.903	-175	3.27	65	0.010	-16	0.871	-175
250	0.912	-176	2.50	58	0.010	-21	0.877	-175
300	0.921	-176	1.99	52	0.009	-24	0.882	-175
350	0.927	-177	1.62	47	0.008	-27	0.883	-176
400	0.936	-178	1.35	42	0.007	-29	0.886	-177
450	0.943	-178	1.13	38	0.006	-29	0.904	-178
500	0.946	-179	0.97	34	0.006	-29	0.920	-179
550	0.952	-180	0.83	31	0.005	-26	0.935	-179
600	0.955	180	0.72	27	0.004	-23	0.955	-180
650	0.957	179	0.64	24	0.004	-17	0.965	-179
700	0.961	179	0.56	22	0.003	-8	0.967	-179
750	0.963	178	0.50	19	0.003	2	0.970	-179
800	0.965	178	0.45	17	0.003	14	0.968	-179
850	0.968	177	0.41	15	0.003	27	0.953	-179
900	0.969	176	0.37	13	0.003	36	0.949	180
950	0.970	176	0.34	11	0.003	45	0.943	179
1000	0.971	175	0.31	9	0.003	54	0.930	178

8 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Table 12. PowerSO-10RF Formed lead (Gull Wing) Mechanical data

Dim.	mm.			Inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A1	0	0.05	0.1	0.	0.0019	0.0038
A2	3.4	3.5	3.6	0.134	0.137	0.142
A3	1.2	1.3	1.4	0.046	0.05	0.054
A4	0.15	0.2	0.25	0.005	0.007	0.009
a		0.2			0.007	
b	5.4	5.53	5.65	0.212	0.217	0.221
c	0.23	0.27	0.32	0.008	0.01	0.012
D	9.4	9.5	9.6	0.370	0.374	0.377
D1	7.4	7.5	7.6	0.290	0.295	0.298
E	13.85	14.1	14.35	0.544	0.555	0.565
E1	9.3	9.4	9.5	0.365	0.37	0.375
E2	7.3	7.4	7.5	0.286	0.292	0.294
E3	5.9	6.1	6.3	0.231	0.24	0.247
F		0.5			0.019	
G		1.2			0.047	
L	0.8	1	1.1	0.030	0.039	0.042
R1			0.25			0.01
R2		0.8			0.031	
T	2 deg	5 deg	8 deg	2 deg	5 deg	8 deg
T1		6 deg			6 deg	
T2		10 deg			10 deg	

Note: Resin protrusions not included (max value: 0.15 mm per side)

Figure 23. Package dimensions

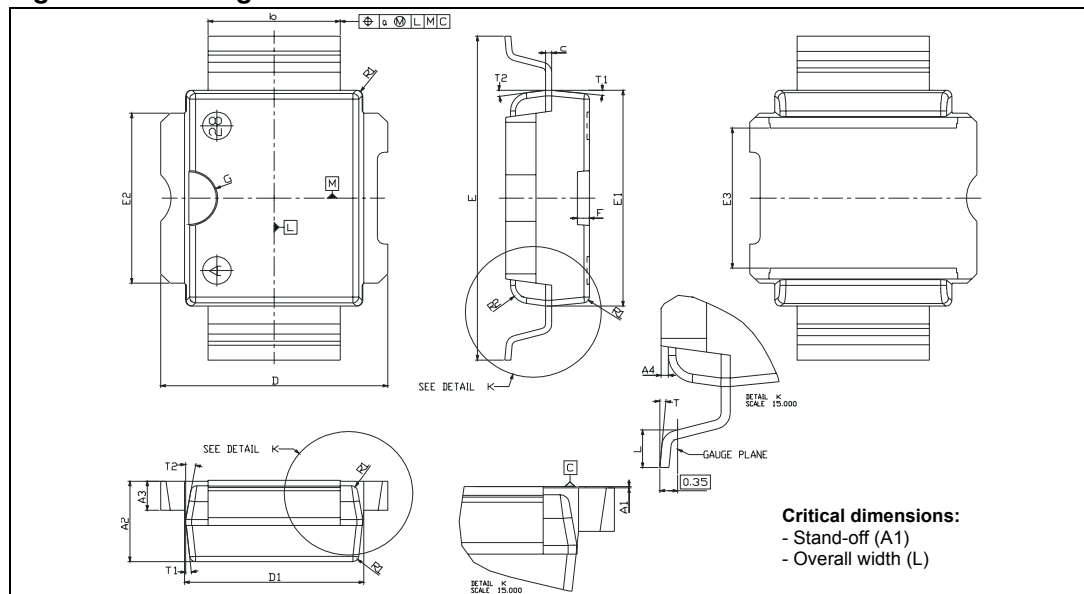


Table 13. PowerSO-10RF Straight Lead Mechanical data

Dim.	mm.			Inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A1	1.62	1.67	1.72	0.064	0.065	0.068
A2	3.4	3.5	3.6	0.134	0.137	0.142
A3	1.2	1.3	1.4	0.046	0.05	0.054
A4	0.15	0.2	0.25	0.005	0.007	0.009
a		0.2			0.007	
b	5.4	5.53	5.65	0.212	0.217	0.221
c	0.23	0.27	0.32	0.008	0.01	0.012
D	9.4	9.5	9.6	0.370	0.374	0.377
D1	7.4	7.5	7.6	0.290	0.295	0.298
E	15.15	15.4	15.65	0.595	0.606	0.615
E1	9.3	9.4	9.5	0.365	0.37	0.375
E2	7.3	7.4	7.5	0.286	0.292	0.294
E3	5.9	6.1	6.3	0.231	0.24	0.247
F		0.5			0.019	
G		1.2			0.047	
R1			0.25			0.01
R2		0.8			0.031	
T1		6 deg			6 deg	
T2		10 deg			10 deg	

Note: Resin protrusions not included (max value: 0.15 mm per side)

Figure 24. Package dimensions

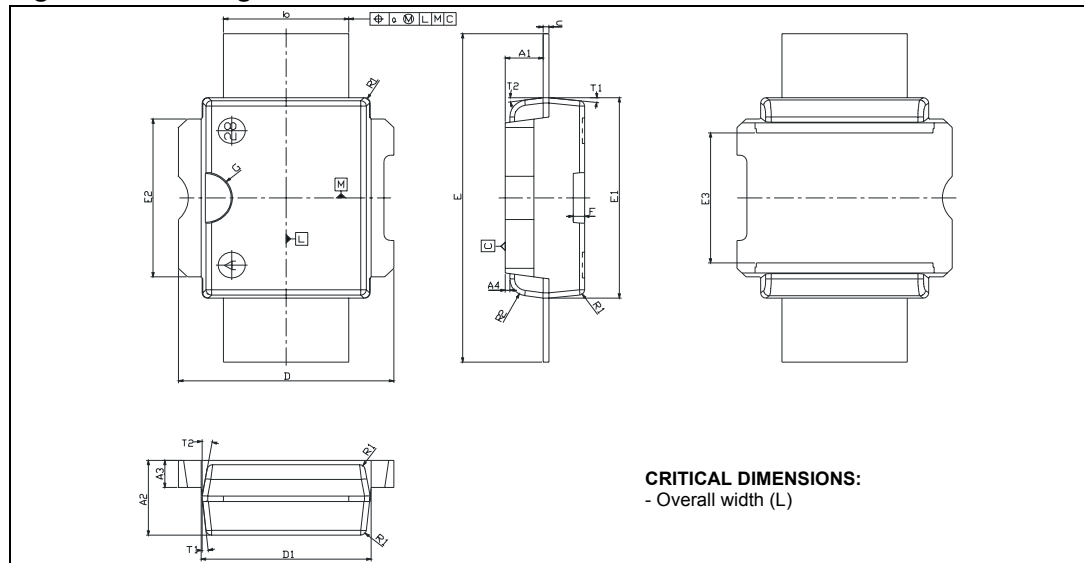


Figure 25. Tube information

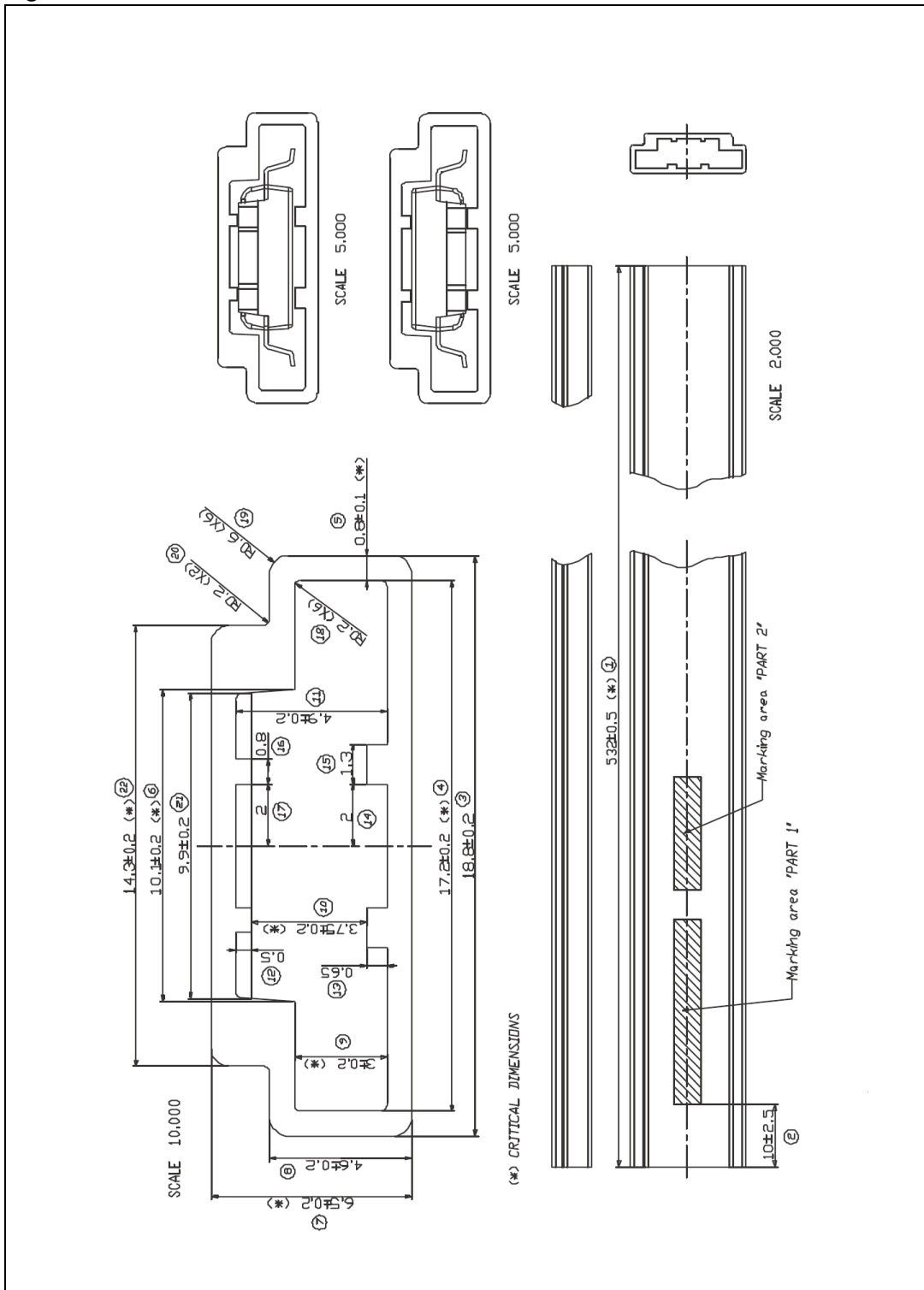
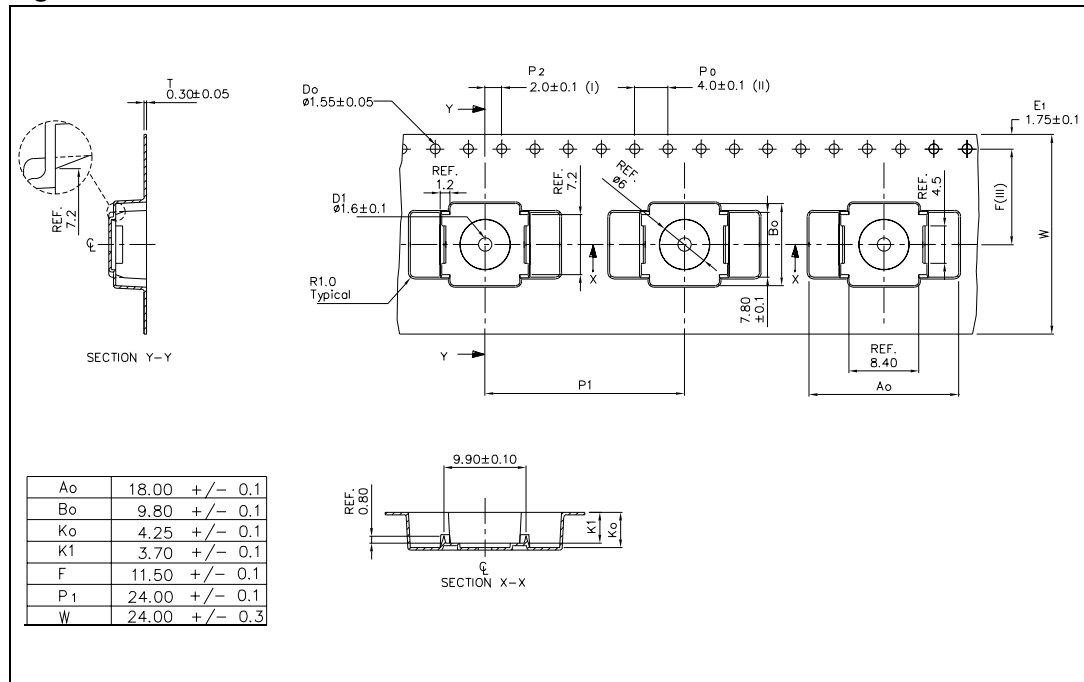


Figure 26. Reel information



9 Revision history

Table 14. Revision history

Date	Revision	Changes
29-Apr-2006	1	Initial release.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED REPRESENTATIVE OF ST, ST PRODUCTS ARE NOT DESIGNED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS, WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com